

**A NITRIDE SEMICONDUCTOR LIGHT EMITTING DEVICE
HAVING A SILVER P-CONTACT**

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ABSTRACT OF THE DISCLOSURE

A light emitting device is constructed on a substrate. The device includes an n-type semiconductor layer in contact with the substrate, an active layer for generating light, the active layer being in electrical contact with the n-type semiconductor layer. A p-type semiconductor layer is in electrical contact with the active layer, and a p-electrode is in electrical contact with the p-type semiconductor layer. The p-electrode includes a layer of silver in contact with the p-type semiconductor layer. A bonding layer is formed overlying the silver layer to make an electrical connection to the silver layer. The silver layer may be thin and transparent or thicker (greater than 20nm) and reflective.

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